

*MEMORY***CMOS 8M × 32
FAST PAGE MODE DRAM MODULE****MB85392A-60/-70****CMOS 4M × 32 Bit Fast Page Mode DRAM Module****DESCRIPTION**

The Fujitsu MB85392A is a fully decoded, CMOS Dynamic Random Access Memory (DRAM) module consisting of sixteen MB8117400A devices. The MB85392A is optimized for those applications requiring high speed, high performance and large memory storage. The operation and electrical characteristics of the MB85392A are the same as the MB8117400A which features fast page mode operation. For ease of memory expansion, the MB85392A is offered in a 72-pad Single In-line Memory Module package (SIMM).

ABSOLUTE MAXIMUM RATINGS (See NOTE.)

Parameter	Symbol	Value	Unit
Supply Voltage	V_{CC}	-0.5 to +7.0	V
Input Voltage	V_{IN}	-0.5 to +7.0	V
Output Voltage	V_{OUT}	-0.5 to +7.0	V
Short Circuit Output Current	I_{OUT}	50	mA
Power Dissipation	P_D	16	W
Storage Temperature	T_{STG}	-55 to +125	°C

NOTE: Permanent device damage may occur if the above **Absolute Maximum Ratings** are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

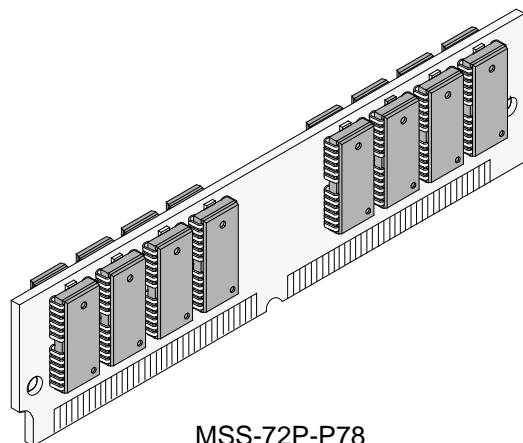
MB85392A-60/MB85392A-70

■ PRODUCT LINE & FEATURES

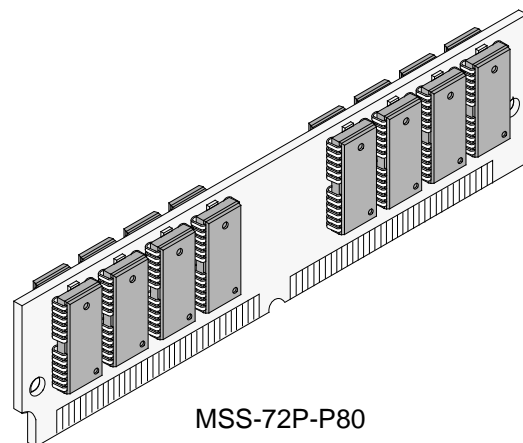
Parameter		MB85392A-60	MB85392A-70
RAS Access Time		60 ns max.	70 ns max.
Random Cycle Time		110 ns min.	130 ns min.
Address Access Time		30 ns max.	35 ns max.
CAS Access Time		15 ns max.	17 ns max.
Fast Page Mode Cycle Time		40 ns min.	45 ns min.
Power Dissipation	Operating Mode	4708 mW max.	4048 mW max.
	Standby Mode	88mW(CMOS) / 176mW(TTL)	

- Organization :
8,388,608 words x 32 bit
- Memory : MB8117400A, 16 pcs
- Decoupling Capacitor, 16 pcs
- 5.0V ± 10% Supply Voltage
- Fast Page operation
- 2,048 Refresh Cycles / 32.8ms
- Package and Ordering Information:
72-pad SIMM, order as
MB85392A-xxPJPB
(PJPB = Solder Pad
MB85392A-xxPJPBK
(PJPBK = Gold Pad

■ PACKAGE



MSS-72P-P78



MSS-72P-P80

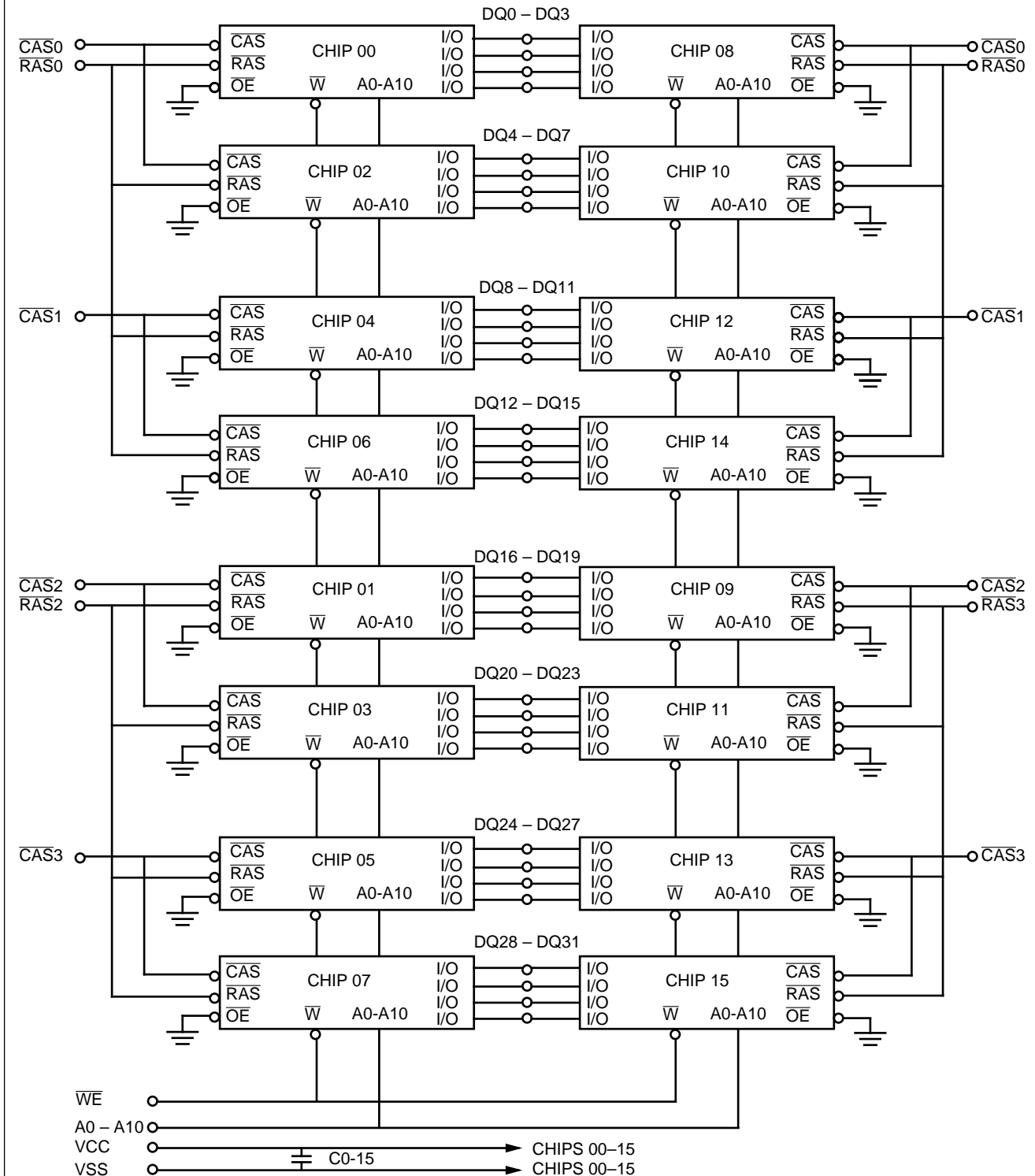
■ PIN ASSIGNMENT

DQ0	2	1	VSS
DQ1	4	3	DQ16
DQ2	6	5	DQ17
DQ3	8	7	DQ18
VCC	10	9	DQ19
A0	12	11	NC
A2	14	13	A1
A4	16	15	A3
A6	18	17	A5
DQ4	20	19	A10
DQ5	22	21	DQ20
DQ6	24	23	DQ21
DQ7	26	25	DQ22
A7	28	27	DQ23
VCC	30	29	NC
A9	32	31	A8
RAS2	34	33	RAS3
NC	36	35	NC
NC	38	37	NC
CAS0	40	39	VSS
CAS3	42	41	CAS2
RAS0	44	43	CAS1
NC	46	45	RAS1
NC	48	47	WE
DQ24	50	49	DQ8
DQ25	52	51	DQ9
DQ26	54	53	DQ10
DQ27	56	55	DQ11
DQ28	58	57	DQ12
DQ29	60	59	VCC
DQ30	62	61	DQ13
DQ31	64	63	DQ14
NC	66	65	DQ15
PD2	68	67	PD1
PD4	70	69	PD3
VSS	72	71	NC

Pin #	Symbol	-60	-70
67	PD1	NC	NC
68	PD2	Vss	Vss
69	PD3	NC	Vss
70	PD4	NC	NC

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FUNCTIONAL BLOCK DIAGRAM



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RECOMMENDED OPERATING CONDITIONS

(Referenced to V_{SS})

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Ground	V_{SS}	0	0	0	V
Input High Voltage, all inputs	V_{IH}	2.4	—	6.5	V
Input Low Voltage, all inputs*	V_{IL}	-0.3	—	0.8	V
Ambient Temperature	T_A	0	25	70	°C

Note: *Undershoots of up to -2.0 volts with a pulse width not exceeding 10ns are acceptable.

DC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

Parameter	Symbol	Test Condition	Min.	Max.	Unit
Output High Voltage* ¹	V_{OH}	$I_{OH} = -5 \text{ mA}$	2.4	—	V
Output Low Voltage* ¹	V_{OL}	$I_{OL} = 4.2 \text{ mA}$	—	0.4	V
Input Leakage Current	RAS0 – RAS3	$0 \text{ V} \leq V_{IN} \leq 5.5 \text{ V}$, $4.5 \text{ V} \leq V_{CC} \leq 5.5 \text{ V}$, $V_{SS} = 0 \text{ V}$, all other pins not under test = 0 V	-30	30	μA
	CAS0 – CAS3		-30	30	
	Address, \overline{WE}		-90	90	
Output Leakage Current	I_{OL}	$0 \text{ V} \leq V_{OUT} \leq 5.5 \text{ V}$, $4.5 \text{ V} \leq V_{CC} \leq 5.5 \text{ V}$, Data out disabled	-20	20	μA
Operating Current* ² (Average power supply current)	MB85392A-60	\overline{RAS} & \overline{CAS} cycling, $t_{RC} = \text{min.}$	—	856	mA
	MB85392A-70		—	736	
Standby Current* ² (Power supply current)	TTL Level	$\overline{RAS} = \overline{CAS} = V_{IH}$ $\overline{RAS} = \overline{CAS} \geq V_{CC} - 0.2 \text{ V}$	—	32	mA
	CMOS Level		—	16	
Refresh Current #1* ² (Average power supply current)	MB85392A-60	$\overline{CAS} = V_{IH}$, $\overline{RAS} = \text{cycling}$, $t_{RC} = \text{min.}$	—	856	mA
	MB85392A-70		—	736	
Fast Page Mode Current* ²	MB85392A-60	$\overline{RAS} = V_{IL}$, $\overline{CAS} = \text{cycling}$, $t_{RC} = \text{min.}$	—	576	mA
	MB85392A-70		—	536	
Refresh Current #2* ² (Average power supply current)	MB85392A-60	$\overline{RAS} = \text{cycling}$, \overline{CAS} -before- \overline{RAS} , $t_{RC} = \text{min.}$	—	856	mA
	MB85392A-70		—	736	

Notes: *1. Referenced to V_{SS} .

*2. I_{CC} depends on the output load conditions and cycle rate. The specific values are obtained with the output open.

I_{CC} depends on the number of address change as $\overline{RAS} = V_{IL}$ and $\overline{CAS} = V_{IH}$, $V_{IL} > -0.3 \text{ V}$.

I_{CC1} , I_{CC3} , and I_{CC5} are specified at one time of address change during $\overline{RAS} = V_{IL}$ and $\overline{CAS} = V_{IH}$.

I_{CC4} is specified at one time of address change during one Page cycle.

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■ AC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.) Notes 1, 2, 3

No.	Parameter	Symbol	MB85392A-60		MB85392A-70		Unit	Notes
			Min.	Max.	Min.	Max.		
1	Time Between Refresh	t_{REF}	—	32.8	—	32.8	ms	
2	Random Read/Write Cycle Time	t_{RC}	110	—	130	—	ns	
3	Access Time from \overline{RAS}	t_{RAC}	—	60	—	70	ns	4, 7
4	Access Time from \overline{CAS}	t_{CAC}	—	15	—	17	ns	5, 7
5	Column Address Access Time	t_{AA}	—	30	—	35	ns	6, 7
6	Output Hold Time	t_{OH}	3	—	3	—	ns	
7	Output Buffer Turn On Delay Time	t_{ON}	0	—	0	—	ns	
8	Output Buffer Turn Off Delay Time	t_{OFF}	—	15	—	17	ns	8
9	Transition Time	t_T	3	50	3	50	ns	
10	\overline{RAS} Precharge Time	t_{RP}	40	—	50	—	ns	
11	\overline{RAS} Pulse Width	t_{RAS}	60	100000	70	100000	ns	
12	\overline{RAS} Hold Time	t_{RSH}	15	—	17	—	ns	
13	\overline{CAS} to \overline{RAS} Precharge Time	t_{CRP}	0	—	0	—	ns	
14	\overline{RAS} to \overline{CAS} Delay Time	t_{RCD}	20	45	20	53	ns	9, 10
15	\overline{CAS} Pulse Width	t_{CAS}	15	10000	17	10000	ns	
16	\overline{CAS} Hold Time	t_{CSH}	60	—	70	—	ns	
17	\overline{CAS} Precharge Time (C-B-R Refresh)	t_{CPN}	10	—	10	—	ns	17
18	Row Address Setup Time	t_{ASR}	0	—	0	—	ns	
19	Row Address Hold Time	t_{RAH}	10	—	10	—	ns	
20	Column Address Setup Time	t_{ASC}	0	—	0	—	ns	
21	Column Address Hold Time	t_{CAH}	15	—	15	—	ns	
22	Column Address Hold Time from \overline{RAS}	t_{AR}	35	—	35	—	ns	
23	\overline{RAS} to Column Address Delay Time	t_{RAD}	15	30	15	35	ns	11
24	Column Address to \overline{RAS} Lead Time	t_{RAL}	30	—	35	—	ns	
25	Column Address to \overline{CAS} Lead Time	t_{CAL}	30	—	35	—	ns	
26	Read Command Setup Time	t_{RCS}	0	—	0	—	ns	
27	Read Command Hold Time Referenced to \overline{RAS}	t_{RRH}	0	—	0	—	ns	12
28	Read Command Hold Time Referenced to \overline{CAS}	t_{RCH}	0	—	0	—	ns	12
29	Write Command Setup Time	t_{WCS}	0	—	0	—	ns	13
30	Write Command Hold Time	t_{WCH}	15	—	15	—	ns	

(Continued)

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(Continued)

No.	Parameter	Symbol	MB85392A-60		MB85392A-70		Unit	Notes
			Min.	Max.	Min.	Max.		
31	Write Command Hold Time from $\overline{\text{RAS}}$	t_{WCR}	35	—	35	—	ns	
32	$\overline{\text{WE}}$ Pulse Width	t_{WP}	15	—	15	—	ns	
33	Write Command to $\overline{\text{RAS}}$ Lead Time	t_{RWL}	15	—	17	—	ns	
34	Write Command to $\overline{\text{CAS}}$ Lead Time	t_{CWL}	15	—	17	—	ns	
35	DIN Setup Time	t_{DS}	0	—	0	—	ns	
36	DIN Hold Time	t_{DH}	15	—	15	—	ns	
37	Data Hold Time from $\overline{\text{RAS}}$	t_{DHR}	35	—	35	—	ns	
38	$\overline{\text{RAS}}$ Precharge Time to $\overline{\text{CAS}}$ Active Time (Refresh Cycles)	t_{RPC}	5	—	5	—	ns	
39	$\overline{\text{CAS}}$ Setup Time (C-B-R Refresh)	t_{CSR}	0	—	0	—	ns	
40	$\overline{\text{CAS}}$ Hold Time (C-B-R Refresh)	t_{CHR}	10	—	12	—	ns	
41	$\overline{\text{WE}}$ Setup Time from $\overline{\text{RAS}}$	t_{WSR}	0	—	0	—	ns	18
42	$\overline{\text{WE}}$ Hold Time from $\overline{\text{RAS}}$	t_{WHR}	10	—	10	—	ns	18
43	DIN to $\overline{\text{CAS}}$ Delay Time	t_{DZC}	0	—	0	—	ns	15
44	Fast Page Mode $\overline{\text{RAS}}$ Pulse Width	t_{RASP}	—	100000	—	100000	ns	
45	Fast Page Mode Read/Write Cycle Time	t_{PC}	40	—	45	—	ns	
46	Access Time from $\overline{\text{CAS}}$ Precharge	t_{CPA}	—	35	—	40	ns	7, 16
47	Fast Page Mode $\overline{\text{CAS}}$ Precharge Time	t_{CP}	10	—	10	—	ns	
48	Fast Page Mode $\overline{\text{RAS}}$ Hold Time from $\overline{\text{CAS}}$ Precharge	t_{RHCP}	35	—	40	—	ns	

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- Notes: 1. An initial pause ($\overline{\text{RAS}} = \overline{\text{CAS}} = V_{\text{IH}}$) of 200 μs is required after power-up followed by any eight $\overline{\text{RAS}}$ -only cycles before proper device operation is achieved. If an internal refresh counter is used, a minimum of eight $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ initialization cycles are required instead of eight $\overline{\text{RAS}}$ cycles.
2. AC characteristics assume $t_{\text{T}} = 5 \text{ ns}$.
 3. V_{IH} (min.) and V_{IL} (max.) are reference levels for measuring the timing of input signals. Transition times are measured between V_{IH} (min.) and V_{IL} (max.).
 4. Assumes that $t_{\text{RCD}} \leq t_{\text{RCD}} (\text{max.})$, $t_{\text{RAD}} \leq t_{\text{RAD}} (\text{max.})$. If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAC} will be increased by the amount that t_{RCD} exceeds the value shown.
 5. If $t_{\text{RCD}} \geq t_{\text{RCD}} (\text{max.})$, $t_{\text{RAD}} \geq t_{\text{RAD}} (\text{max.})$, and $t_{\text{ASC}} \geq t_{\text{AA}} - t_{\text{CAC}} - t_{\text{T}}$, access time is t_{CAC} .
 6. If $t_{\text{RAD}} \geq t_{\text{RAD}} (\text{max.})$ and $t_{\text{ASC}} \leq t_{\text{AA}} - t_{\text{CAC}} - t_{\text{T}}$, access time is t_{AA} .
 7. Measured with a load equivalent to two TTL loads and 100 pF.
 8. t_{OFF} and t_{OEZ} are specified that output buffer change to high impedance state.
 9. Operation within the $t_{\text{RCD}} (\text{max.})$ limit ensures that $t_{\text{RAC}} (\text{max.})$ can be met. $t_{\text{RCD}} (\text{max.})$ is specified as a reference point only; if t_{RCD} is greater than the specified $t_{\text{RCD}} (\text{max.})$ limit, access time is controlled exclusively by t_{CAC} or t_{AA} .
 10. $t_{\text{RCD}} (\text{min.}) = t_{\text{RAH}} (\text{min.}) + 2 t_{\text{T}} + t_{\text{ASC}} (\text{min.})$.
 11. Operation within the $t_{\text{RAD}} (\text{max.})$ limit ensures that $t_{\text{RAC}} (\text{max.})$ can be met. $t_{\text{RAD}} (\text{max.})$ is specified as a reference point only; if t_{RAD} is greater than the specified $t_{\text{RAD}} (\text{max.})$ limit, access time is controlled exclusively by t_{CAC} or t_{AA} .
 12. Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.
 13. t_{WCS} is specified as a reference point only. If $t_{\text{WCS}} \geq t_{\text{WCS}} (\text{min.})$ the data output pin will remain High-Z state through entire cycle.
 14. Assumes that $t_{\text{WCS}} < t_{\text{WCS}} (\text{min.})$.
 15. Either t_{DZC} or t_{DZO} must be satisfied.
 16. t_{CPA} is access time from the selection of a new column address (caused by changing $\overline{\text{CAS}}$ from "L" to "H"). Therefore, if t_{CP} become long, t_{CPA} also become longer than $t_{\text{CPA}} (\text{max.})$.
 17. Assumes that $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh.
 18. Assumes that test mode function.

*Source: See MB8117400A Data Sheet for details on the electricals.

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■ CAPACITANCE

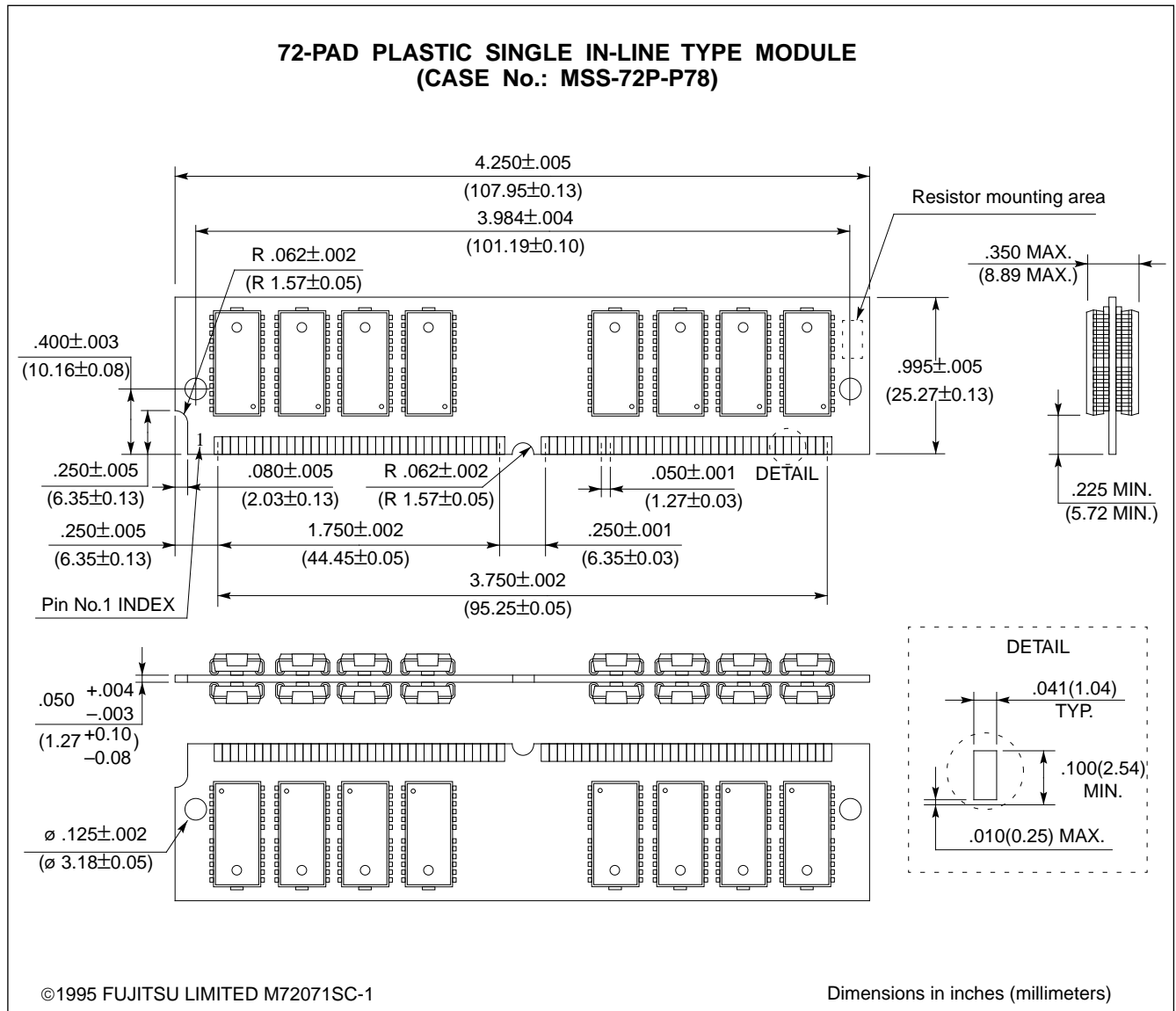
($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

Parameter	Symbol	Min.	Max.	Unit
Input Capacitance, A0 to A10	C_{IN1}	—	113	pF
Input Capacitance, $\overline{RAS0}$ and $\overline{RAS3}$	C_{IN2}	—	39	pF
Input Capacitance, $\overline{CAS0}$ to $\overline{CAS3}$	C_{IN3}	—	34	pF
Input Capacitance, \overline{WE}	C_{IN4}	—	107	pF
I/O Capacitance, (DQ0-31)	C_{DQ}	—	18	pF

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■ PACKAGE DIMENSIONS

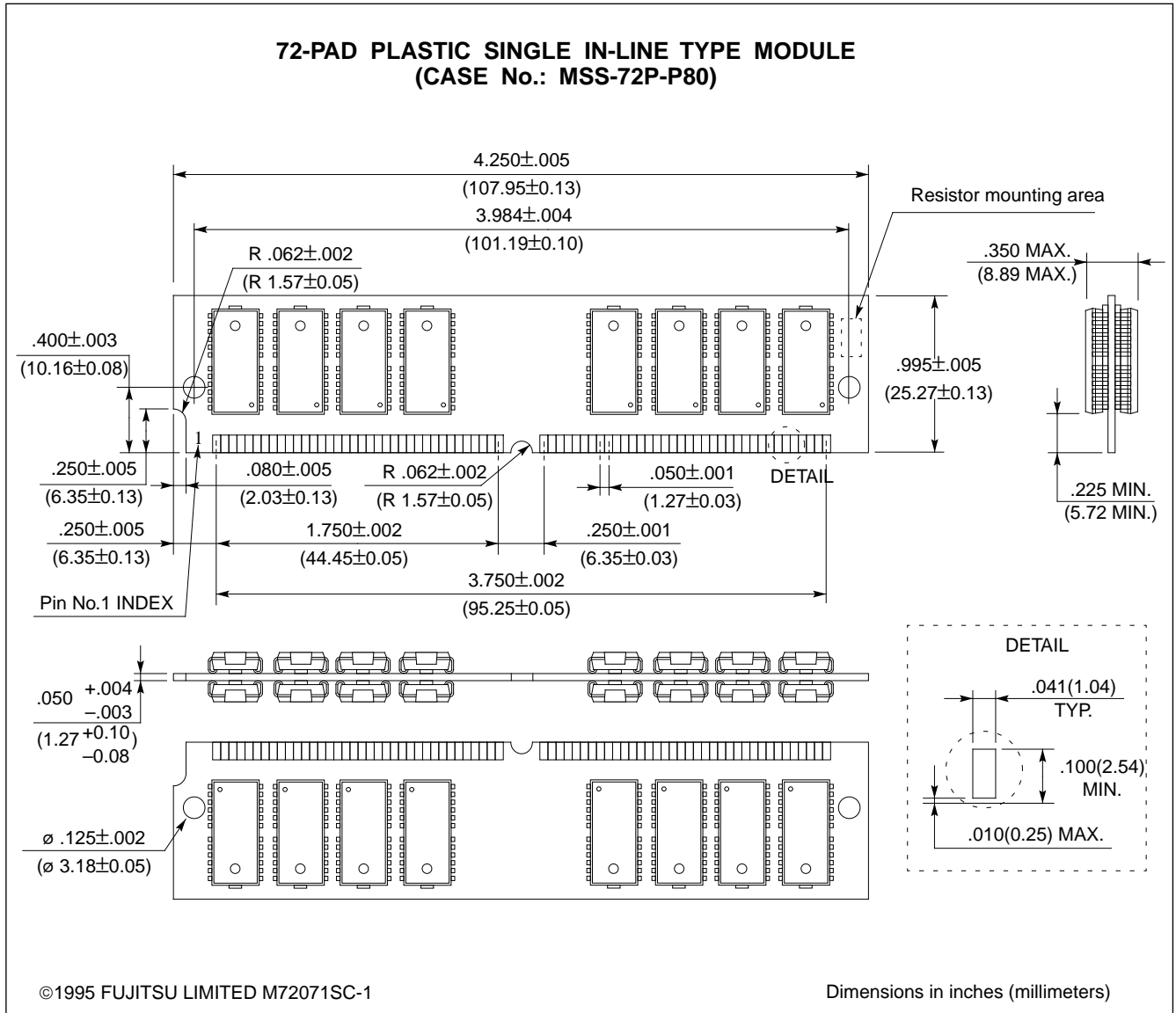
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■ PACKAGE DIMENSIONS (Continued)

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